

OK to
enter
MS
2/6/04

In the Claims

Applicant has submitted a new complete claim set showing marked up claims with insertions indicated by underlining and deletions indicated by strikeouts and/or double bracketing.

B1

1-10. (Cancelled).

11. (Original) A method comprising:

forming defects in a region of a substrate; and

depositing a silicon layer on the region at a temperature of less than 750 °C.

12. (Currently Amended) The method of claim 11, comprising depositing the silicon layer ~~at a~~ temperature prior to annealing the substrate.

13. (Original) The method of claim 11, comprising depositing the silicon layer in a reducing environment.

14. (Original) The method of claim 13, wherein the reducing atmosphere comprises a mixture of hydrogen and silane.

15. (Original) The method of claim 11, comprising depositing the silicon layer at a pressure of less than about 0.1×10^5 Pa.

16. (Original) The method of claim 11, comprising forming defects in an implantation process.

17. (Original) The method of claim 16, comprising forming defects by implanting atoms.

18. (Original) The method of claim 16, comprising forming defects by implanting ions.

OK to
Enter WW
2/6/04

In the Claims

1-10. (Cancelled).

11. (Currently Amended) A method comprising:

forming defects in a region of a substrate by implanting electrically neutral species; and
depositing a silicon layer on the region at a temperature of less than 750 °C.

12. (Previously Presented) The method of claim 11, comprising depositing the silicon layer prior
to annealing the substrate.

13. (Original) The method of claim 11, comprising depositing the silicon layer in a reducing
environment.

14. (Original) The method of claim 13, wherein the reducing atmosphere comprises a mixture of
hydrogen and silane.

15. (Original) The method of claim 11, comprising depositing the silicon layer at a pressure of
less than about 0.1×10^5 Pa.

16-19. (Cancelled)

20. (Currently Amended) The method of claim ~~19~~11, comprising forming defects by implanting
fluorine atoms.

21. (Currently Amended) The method of claim ~~16~~11, further comprising depositing an oxide
layer having a thickness of less than 10 nm on the surface of the region prior to the implantation
step and removing the oxide layer after the implantation step.

22. (Original) The method of claim 11, comprising forming defects by an etching process that
directs ions toward the region.